

Supporting Information

Revealing Electronic Structure, Heterojunction Band Offset and Alignment of Cu₂ZnGeSe₄: A Combined Experimental and Computational Study toward Photovoltaic Applications

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Figure S1: The EDS spectra and the elemental mapping suggest even distribution of chemical constituents in CZGSe thin film.

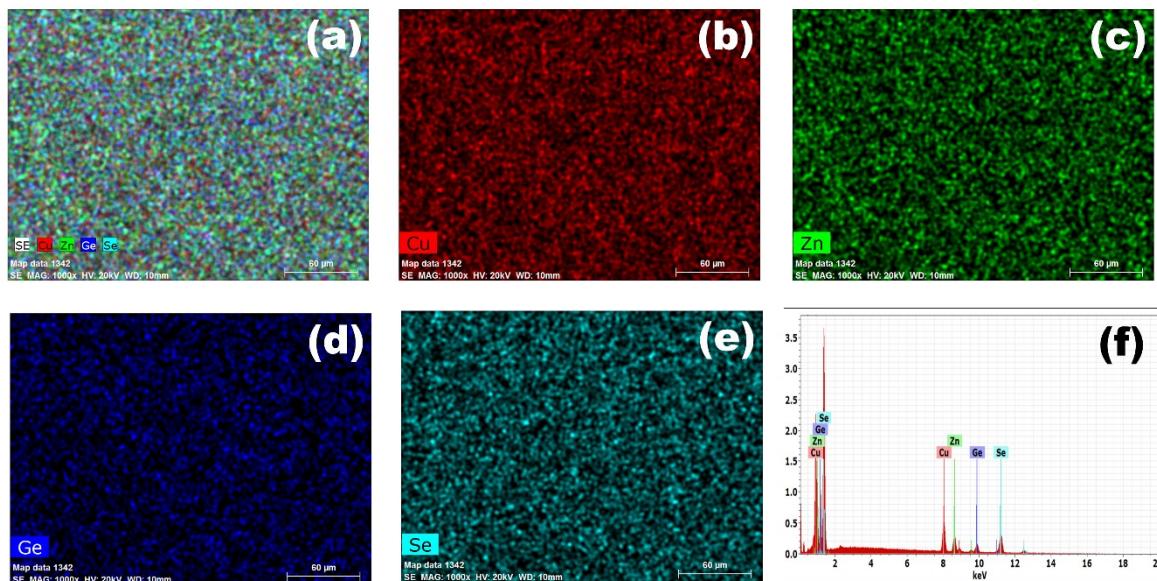


Figure S2: (a, b) SEM images of CZGSe thin film. 2-D (c) and 3-D AFM (d) images CZGSe thin film.

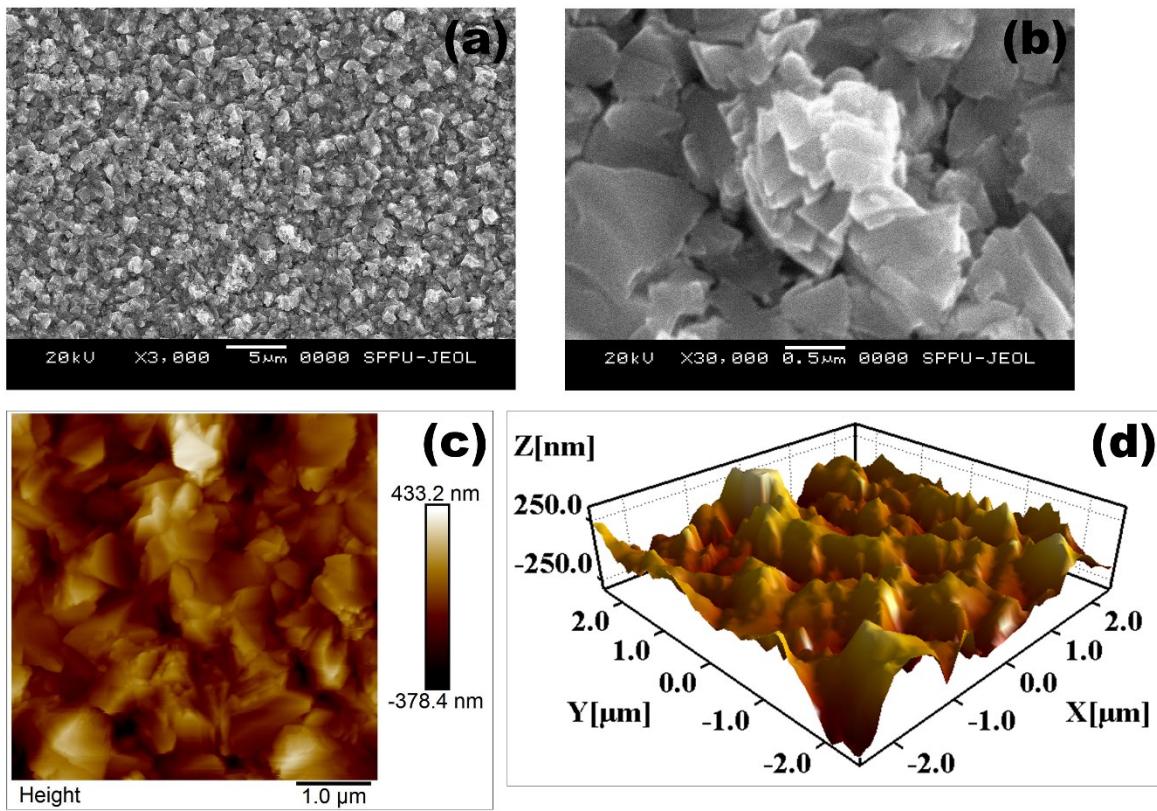


Table S1: Calculated effective masses of holes (m_h^*) and electrons (m_e^*) along the high-symmetry directions of the Brillouin zone of CZGSe.

Direction	$m_h^*(m_e)$	$m_e^*(m_e)$
Z- Γ	0.0036	0.0057
Γ -X	0.0109	0.0099
X-M	0.0525	0.0083
M- Γ	0.0432	0.00342